

# Resistive sensors

Material from

- Section 3.5: Resistivity
- Section 9.5: Strain gauges
- Chapter 10: Pressure sensors
- Chapter 18, 18.3: Micromachining and silicon
- Chapter 5.7: Bridge circuits

# Hvorfor

Noe vi vil måle

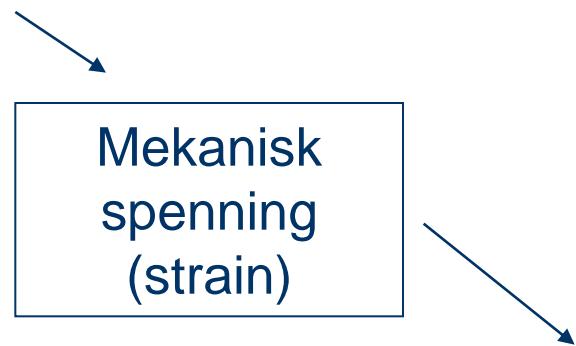
Mekanisk  
spenning  
(strain)

Motstandsendring

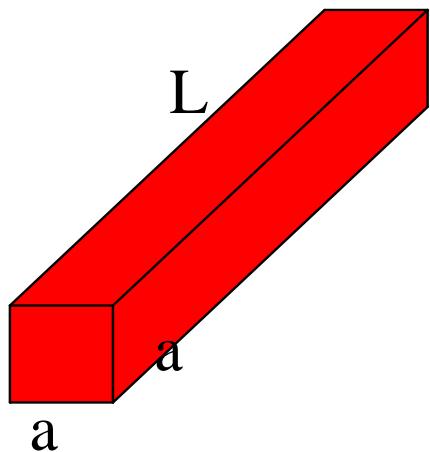
Elektrisk  
spenning

Temperaturendring

Noe annet vi  
vil måle



# Resistivity



$$R_0 = \rho L/a^2$$

$$\rho = \frac{m}{ne^2\tau} \quad (3.53)$$

Time between collisions

Carrier density

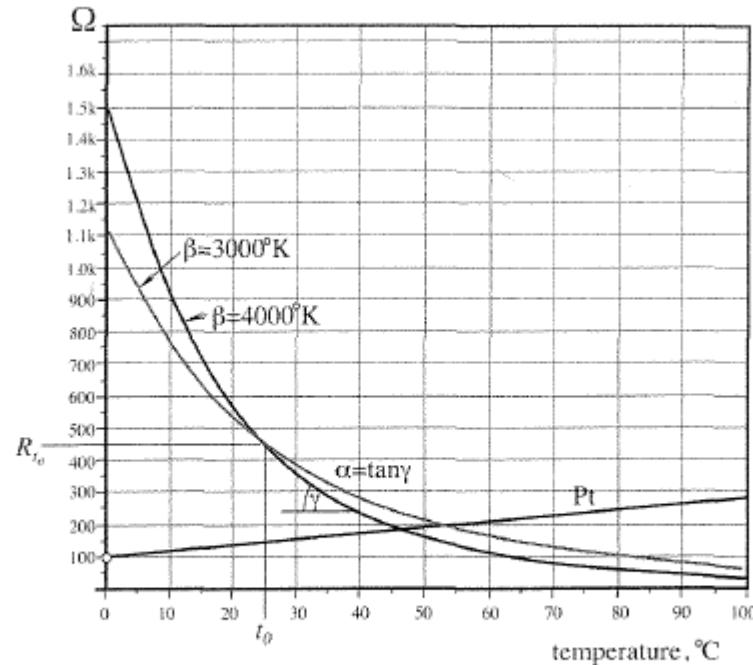
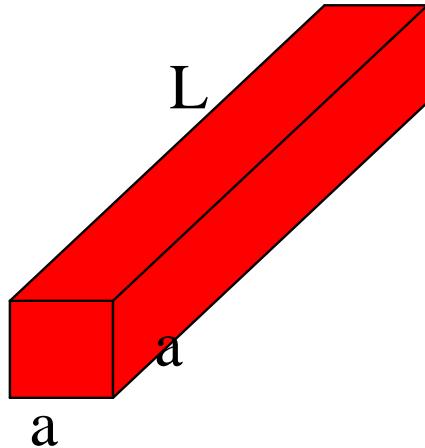


Fig. 3.18. Resistance-temperature characteristics for two thermistors and Pt RTD ( $R_0 = 1k$ ); thermistors are calibrated at  $t_0 = 25^\circ\text{C}$  and RTD at  $0^\circ\text{C}$ .

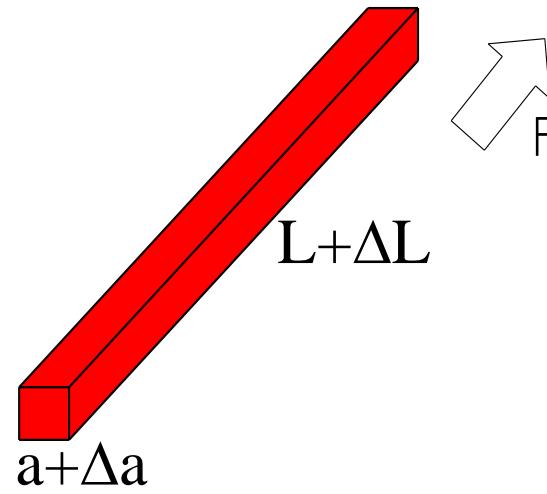
# Begrep

- Resistive thermal detector (RTD)
- Pt 100
- Thermistor
- Temperature coefficient of resistivity (TCR)
- Negative temperature coefficient (NTC)
- Positive temperature coefficient (PTC)

# Motstandsendring i metall leder



$$R_0 = \rho L/a^2$$

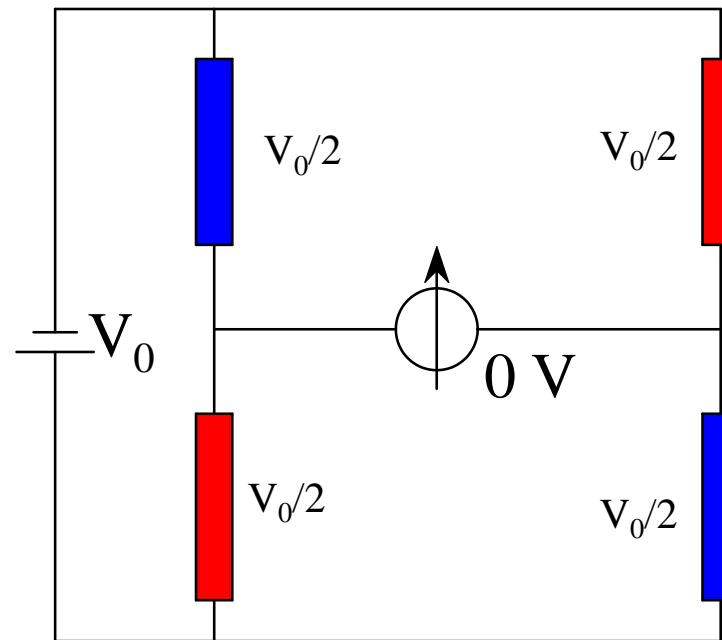


$$R = R_0 + R_0 \Delta L/L - 2R_0 \Delta a/a$$

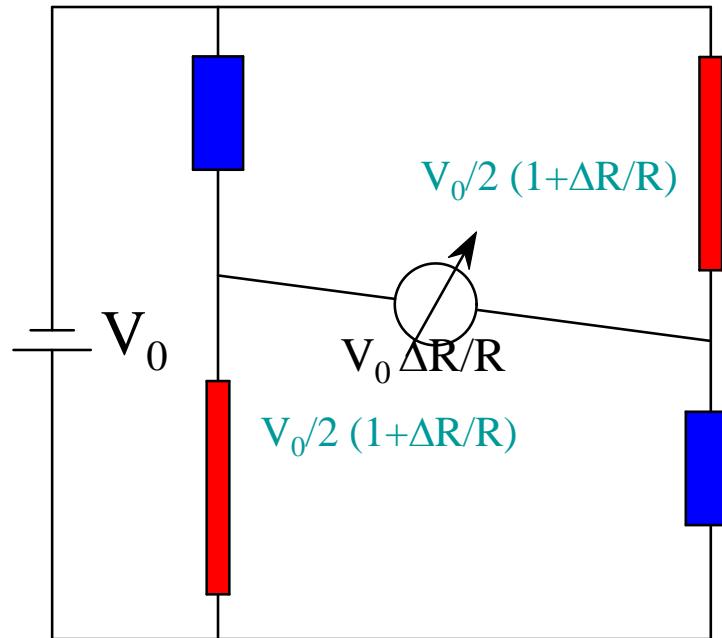
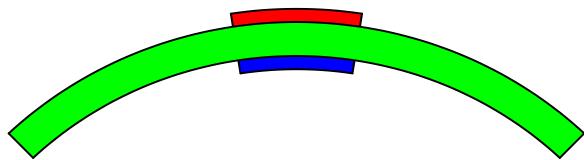
$$\Delta a/a \approx -1/2 \Delta L/L$$

$$\Delta R/R \approx 2 \Delta L/L \quad \Delta R/R \approx 2 \varepsilon$$

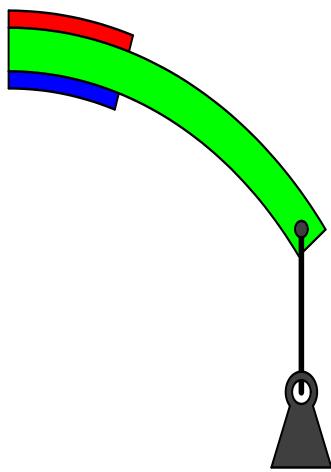
# Balansert bro



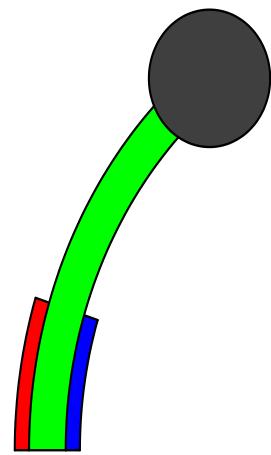
# Belastet struktur



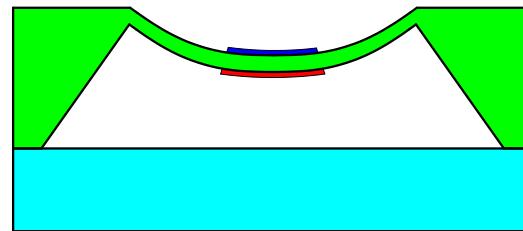
# Bruksområder



Veieceller



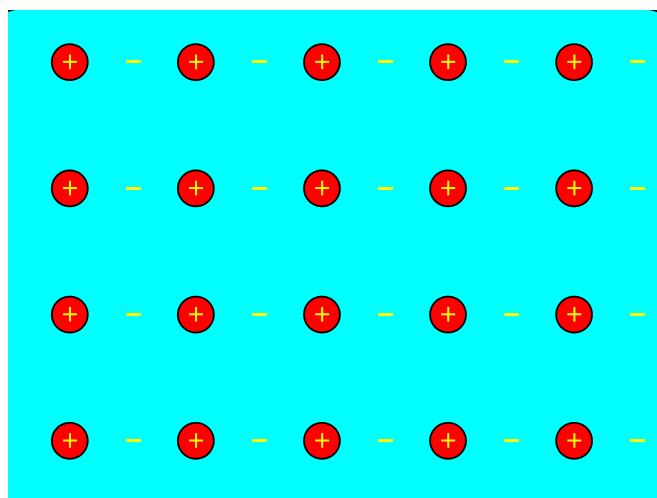
Akselerometer



Trykksensorer

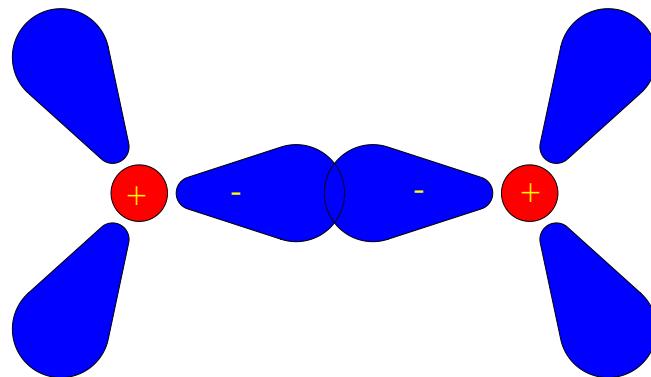
# Forskjell i gauge faktor

Metall:



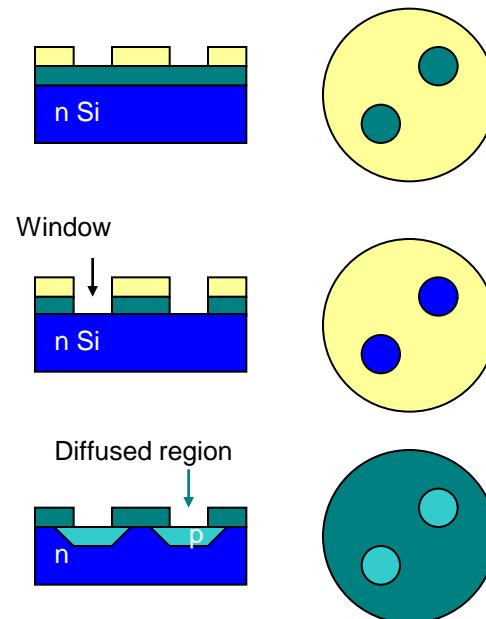
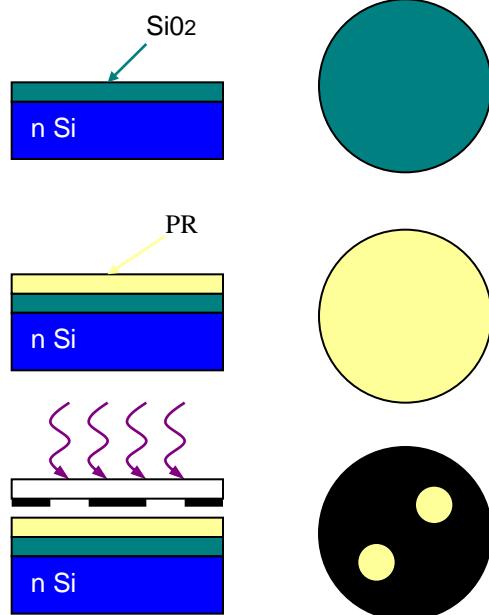
$$\Delta R/R \approx 2 \varepsilon$$

Silisium:



$$\Delta R/R \approx 90 \varepsilon$$

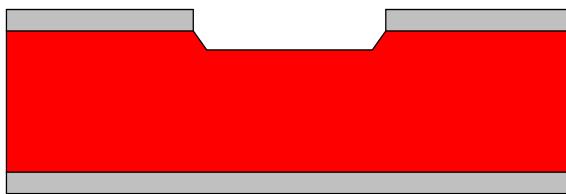
# Fotolitografi



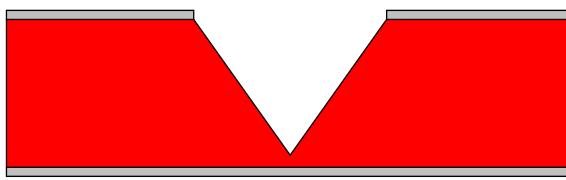
# Anisotrop våt etsing



Silisium oksyd eller nitrid  
åpnet med fotolitografi

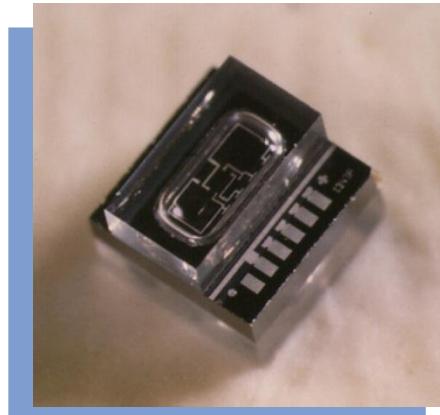
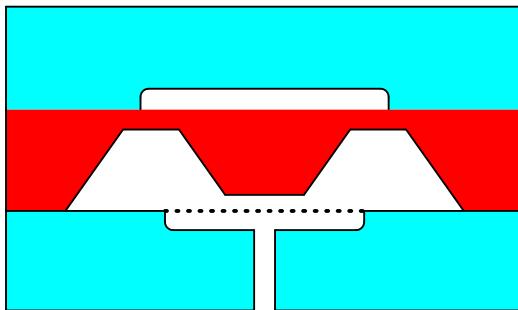
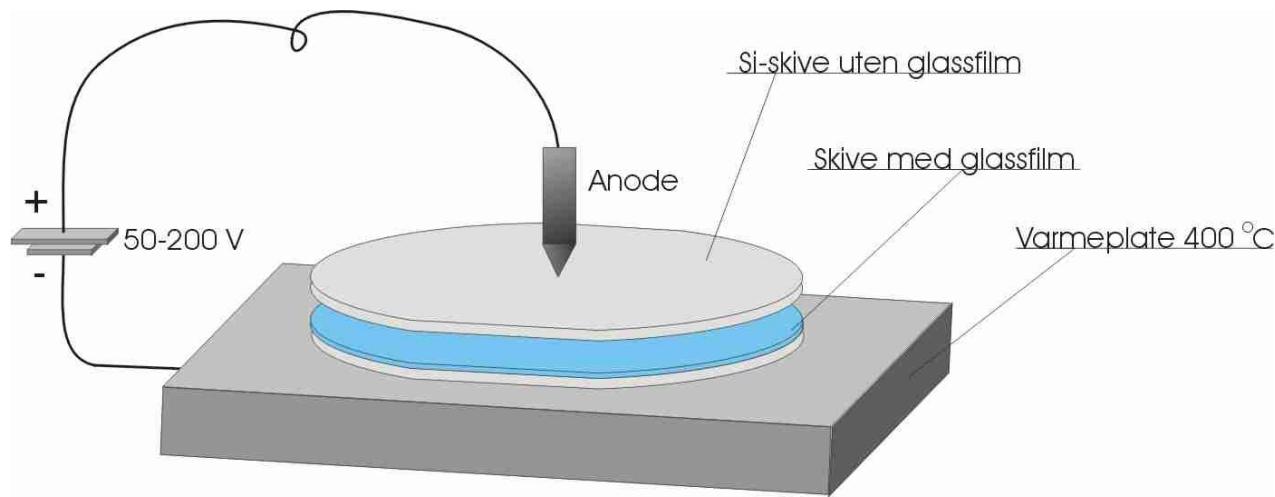


Dypper i KOH/H<sub>2</sub>O

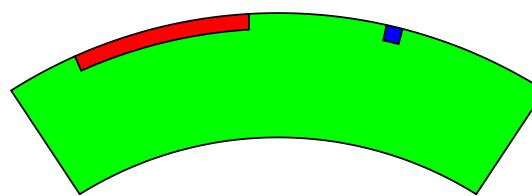
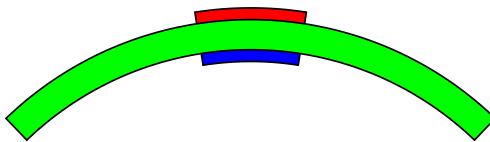


“Lar ligge” i KOH/H<sub>2</sub>O

# Anodisk bonding

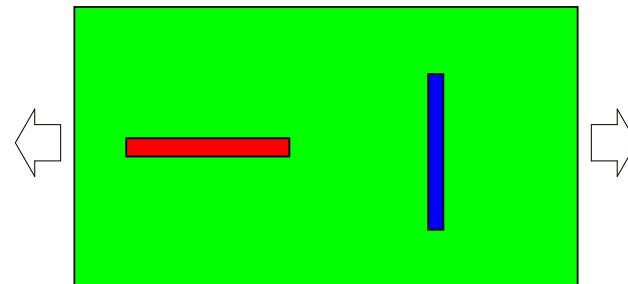


# Retningsavhengighet



Over/under konfigurasjon  
er ikke praktisk i silisium.

Men vi kan snu retningen  
på motstandene



# Piezoresistiv trykksensor

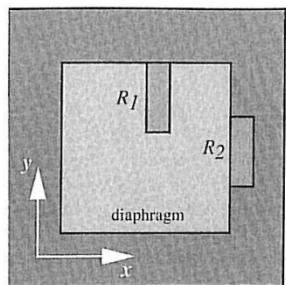
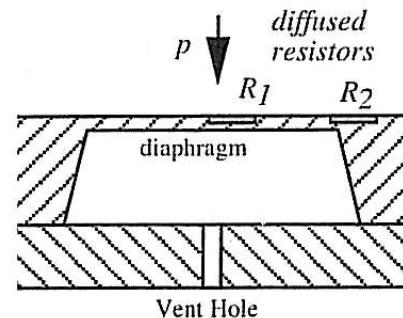
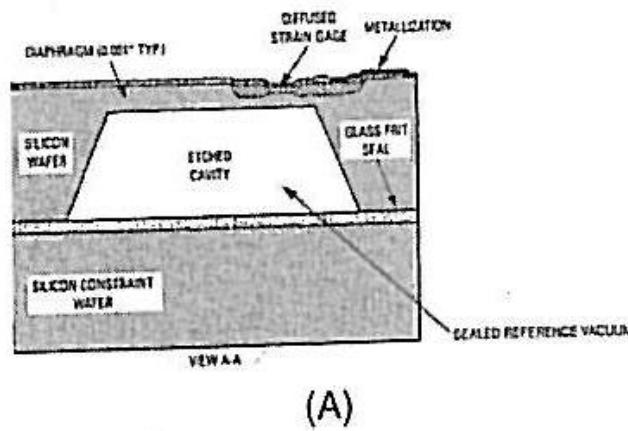


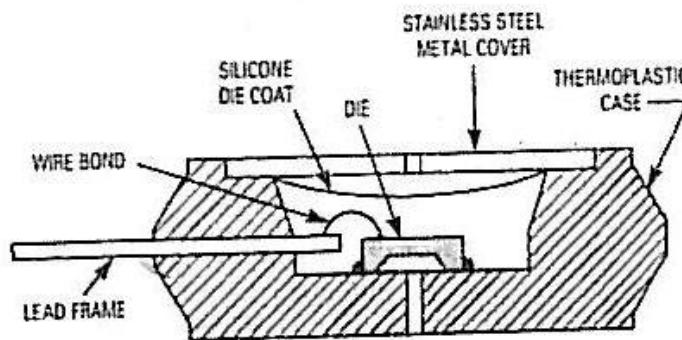
Fig. 10.4. Position of piezoresistors on a silicon diaphragm.



## 348 10 Pressure Sensors



(A)



(B)

Fig. 10.7. Absolute (A) and differential (B) pressure sensor packagings. (Copyright Motorola, Inc. Used with permission.)